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EXAMINING GROUP: 2822

740756-1551

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI et al.

Application No.: 08/691,434

Filed: August 2, 1996

For: METHOD OF FABRICATING
SEMICONDUCTOR DEVICES
AND APPARATUS FOR
PROCESSING A SEMICONDUCTOR

) Art Unit: 2822

) Examiner: Mary Wilczewski

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on 9-24-01

Hansley Strain

AMENDMENT UNDER 37 C.F.R. 1.116

Commissioner of Patents
Washington, D.C. 20231

September 24, 2001

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Dear Sir:

In response to the Examiner's Final Office Action mailed April 24, 2001, the period for responding having been extended two (2) months, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please amend claims 16, 17, 19, 20, 56, 57, 58, 60, 74-77, and 80-85 as follows:

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16. (Amended) An apparatus for processing a semiconductor comprising:

a vacuum chamber;

an ion introducing apparatus connected to said vacuum chamber for doping a semiconductor layer formed over a substrate with a dopant impurity;

a laser processing apparatus comprising a laser processing chamber and a laser for treating said semiconductor layer with a laser light in said laser processing chamber after said doping, said laser processing chamber connected to said ion introducing apparatus through said